

N-Channel Enhancement Mode Power MOSFET

Description

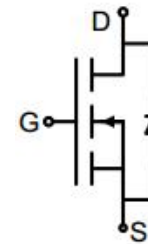
The G800N06H uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

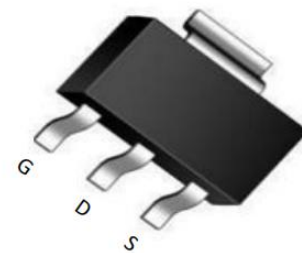
- V_{DS} 60V
- I_D (at $V_{GS} = 10V$) 3A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 80m Ω
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 85m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



SOT-223

Ordering Information

| Device | Package | Marking | Packaging |
|----------|---------|---------|--------------|
| G800N06H | SOT-223 | G800N06 | 2500psc/Reel |

Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise noted

| Parameter | Symbol | Value | Unit |
|--|----------------|------------|------------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Continuous Drain Current | I_D | 3 | A |
| Pulsed Drain Current (note1) | I_{DM} | 12 | A |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Power Dissipation | P_D | 1.2 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 To 150 | $^\circ C$ |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|---|------------|-------|--------------|
| Thermal Resistance, Junction-to-Ambient | R_{thJA} | 104 | $^\circ C/W$ |

| Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|---------------|--|-------|------|-----------|------------|
| Parameter | Symbol | Test Conditions | Value | | | Unit |
| | | | Min. | Typ. | Max. | |
| Static Parameters | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 250\mu A$ | 60 | -- | -- | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 60V, V_{GS} = 0V$ | -- | -- | 1 | μA |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20V$ | -- | -- | ± 100 | nA |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 0.7 | 0.9 | 1.2 | V |
| Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 3A$ | -- | 65 | 80 | m Ω |
| | | $V_{GS} = 4.5V, I_D = 3A$ | -- | 70 | 85 | |
| Forward Transconductance | g_{FS} | $V_{GS} = 5V, I_D = 3A$ | -- | 9 | -- | S |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0\text{MHz}$ | -- | 457 | -- | pF |
| Output Capacitance | C_{oss} | | -- | 25 | -- | |
| Reverse Transfer Capacitance | C_{rss} | | -- | 22 | -- | |
| Total Gate Charge | Q_g | $V_{DD} = 30V,$ $I_D = 3A,$ $V_{GS} = 4.5V$ | -- | 6 | -- | nC |
| Gate-Source Charge | Q_{gs} | | -- | 1 | -- | |
| Gate-Drain Charge | Q_{gd} | | -- | 1.3 | -- | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD} = 30V,$ $I_D = 3A,$ $R_G = 1\Omega$ | -- | 15 | -- | ns |
| Turn-on Rise Time | t_r | | -- | 6 | -- | |
| Turn-off Delay Time | $t_{d(off)}$ | | -- | 15 | -- | |
| Turn-off Fall Time | t_f | | -- | 10 | -- | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Body Diode Current | I_S | $T_C = 25^\circ\text{C}$ | -- | -- | 3 | A |
| Body Diode Voltage | V_{SD} | $T_J = 25^\circ\text{C}, I_{SD} = 3A, V_{GS} = 0V$ | -- | -- | 1.2 | V |
| Reverse Recovery Charge | Q_{rr} | $I_F = 3A, V_{GS} = 0V$ $di/dt = 100A/\mu s$ | -- | 38 | -- | nC |
| Reverse Recovery Time | T_{rr} | | -- | 36 | -- | ns |

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

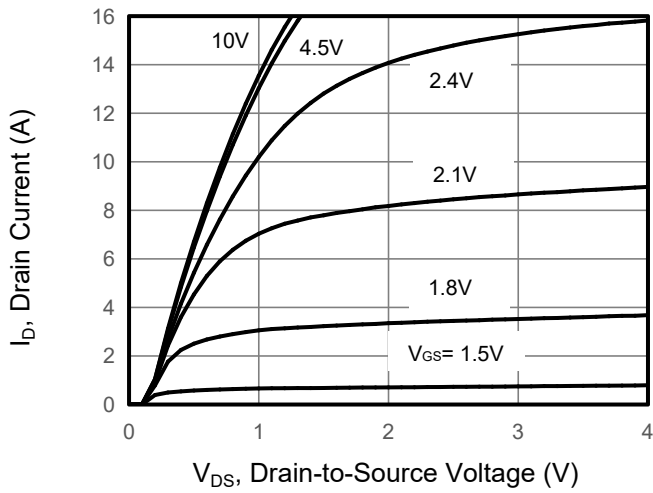


Figure 2. Transfer Characteristics

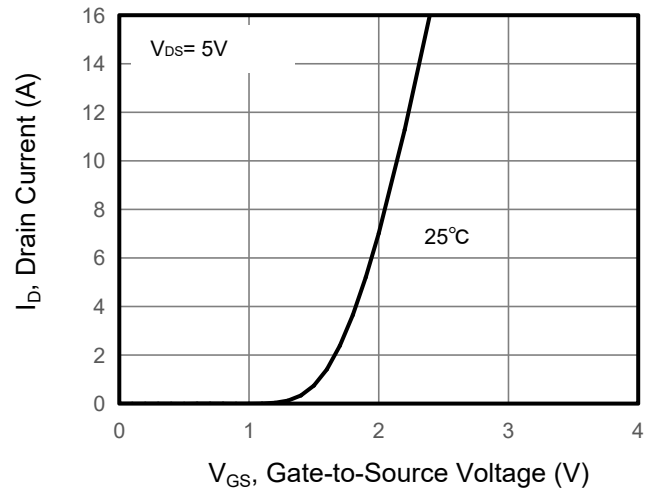


Figure 3. Drain Source On Resistance

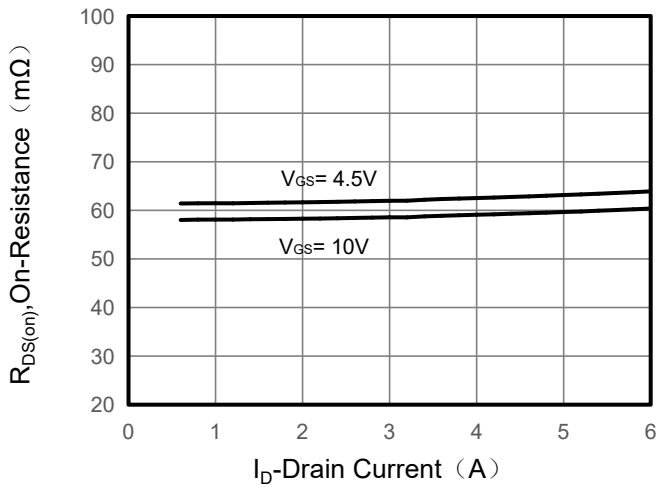


Figure 4. Gate Charge

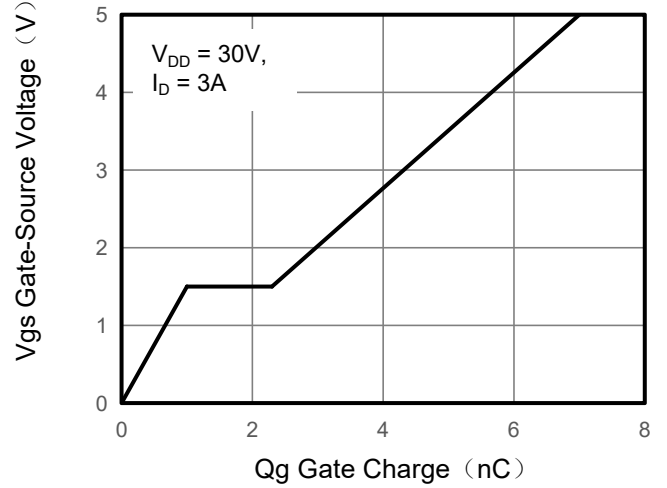


Figure 5. Capacitance

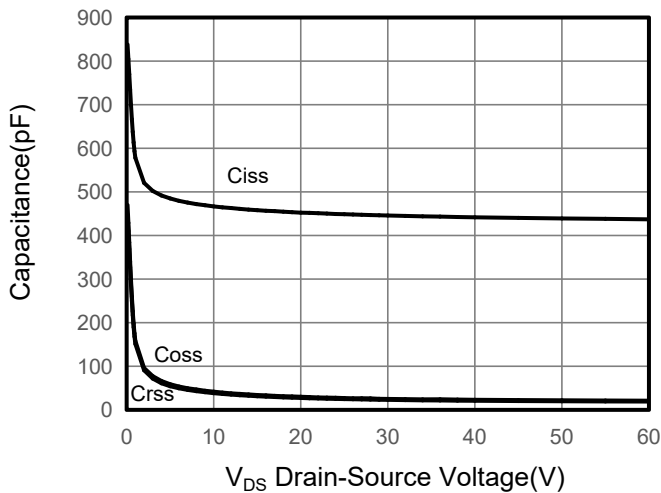
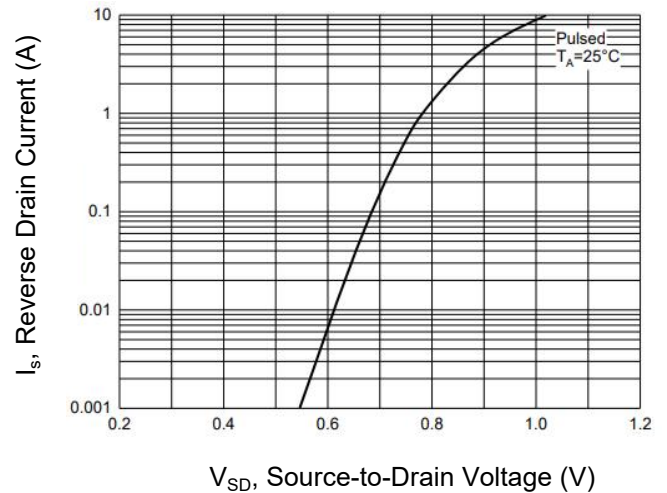


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

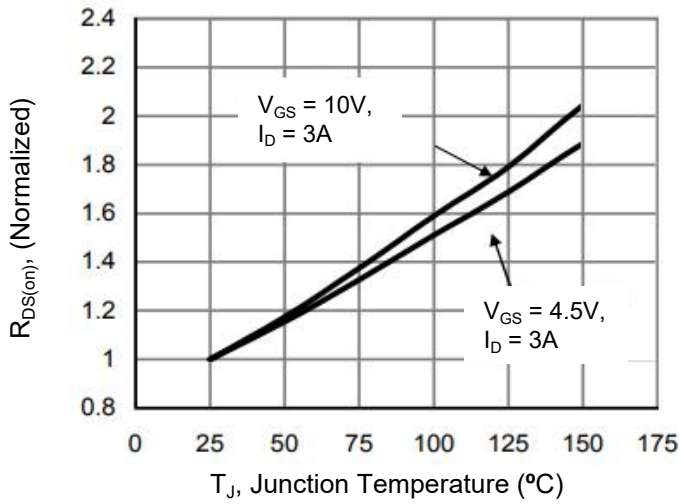


Figure 8. Safe Operation Area

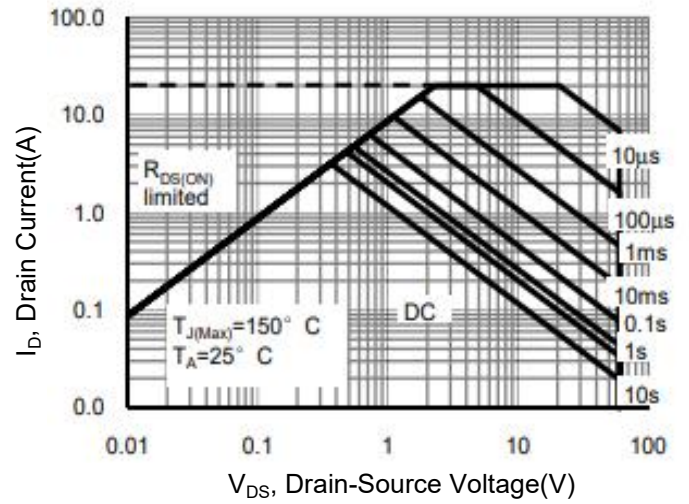
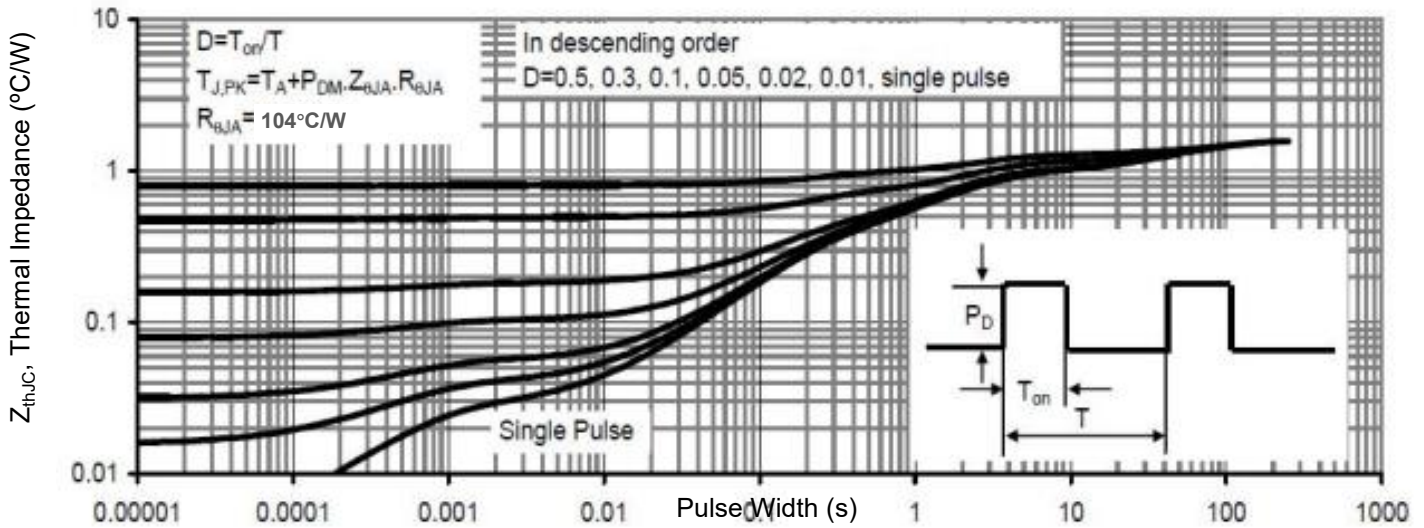
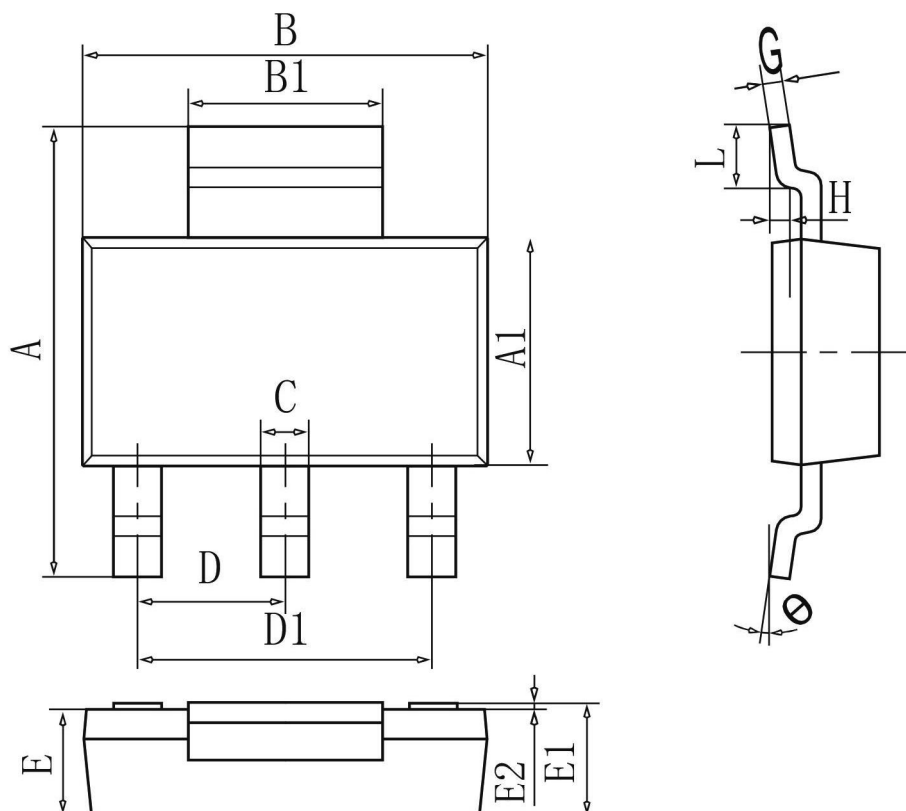


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-223 Package Information



| DIM | MIN | NOM | MAX |
|----------------------|-----------|-------|-------|
| A | 6.80 | 7.00 | 7.20 |
| A1 | 3.30 | 3.50 | 3.70 |
| B | 6.40 | 6.60 | 6.80 |
| B1 | 2.96 | 3.00 | 3.10 |
| C | 0.66 | 0.70 | 0.80 |
| D | 2.25 | 2.30 | 2.35 |
| D1 | 4.60REF | | |
| E | 1.50 | 1.60 | 1.70 |
| E1 | 1.65REF | | |
| E2 | 0.02 | 0.06 | 0.10 |
| G | 0.255 | 0.305 | 0.355 |
| H | 0.25GAUGR | | |
| L | 0.90 | - | - |
| θ | 0° | - | 10° |
| All Dimensions in mm | | | |

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